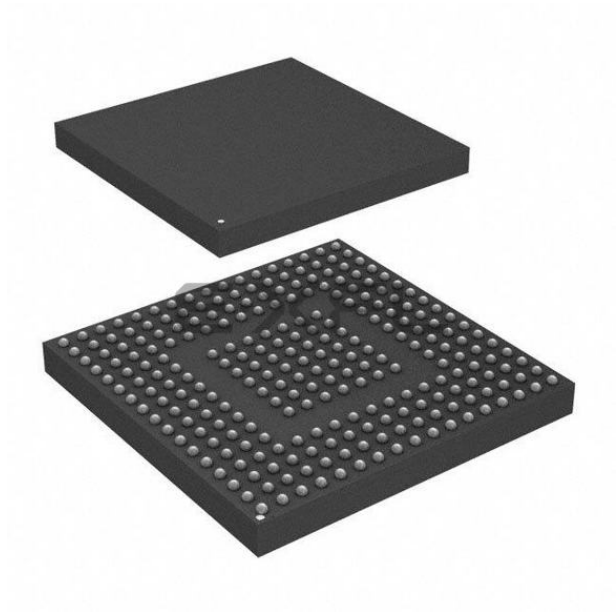

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z7d
Core Size	32-Bit Dual-Core
Speed	150MHz
Connectivity	CANbus, EBI/EMI, Ethernet, FlexRay, I²C, LINbus, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	-
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.14V ~ 5.5V
Data Converters	A/D 22x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	257-LFBGA
Supplier Device Package	257-LFBGA (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5673kf0vmm1r

Table 1. MPC5675K family device comparison (continued)

Features		MPC5673K	MPC5674K	MPC5675K
Modules (cont.)	External Bus Interface (EBI)	1 module[5] 16-bit Data + Address or 32-bit Data with Address bus muxed[8]		
	Fast Ethernet Controller (FEC)	1 module		
	Fault Collection and Control Unit (FCCU)	1 module		
	FlexCAN	4 modules (32 message buffers each)		
	FlexPWM	3 modules (each 4 × 3 channels)		
	FlexRay	Optional		Yes
	I^2C	2 modules[6]	3 modules	
	Interrupt Controller (INTC)	Yes (SoR)		
	LINFlex	3 modules[7]	4 modules	
	Parallel Data Interface (PDI)	1 module[8]		
	Periodic Interrupt Timer (PIT)	1 module, 4 channels		
	Software Watchdog Timer (SWT)	Yes (SoR)		
	System Timer Module (STM)	Yes (SoR)		
	Temperature sensor	1 module		
	Wakeup Unit (WKPU)	Yes		
	Crossbar switch (XBAR)	3 modules, 2 are user-configurable		
Clocking	Clock monitor unit (CMU)	3 modules		
	Frequency-modulated phase-locked loop (FMPLL)	2 modules (system and auxiliary)		
	IRCOSC – 16 MHz	1		
	XOSC 4–40 MHz	1		
Supply	Power management unit (PMU)	Yes		
	1.2 V low-voltage detector (LVD12)	1		
	1.2 V high-voltage detector (HVD12)	1		
	2.7 V low-voltage detector (LVD27)	4		
Debug	Nexus	Class 3+ (for cores and SRAM ports)		

- 16-region MPU with concurrent checks against each master access
- 32-byte granularity for protected address region

1.6.4 Enhanced Direct Memory Access (eDMA) controller

- 32 channels support independent 8-, 16-, 32-bit single value or block transfers
- Supports variable-sized queues and circular queues
- Source and destination address registers are independently configured to post-increment or remain constant
- Each transfer is initiated by a peripheral, CPU, or eDMA channel request
- Each eDMA channel can optionally send an interrupt request to the CPU on completion of a single value or block transfer

1.6.5 Interrupt Controller (INTC)

- 208 peripheral interrupt requests
- 8 software settable sources
- Unique 9-bit vector per interrupt source
- 16 priority levels with fixed hardware arbitration within priority levels for each interrupt source
- Priority elevation for shared resources

1.6.6 Frequency-Modulated Phase-Locked Loop (FMPLL)

Two FMPLLs are available on each device.

Each FMPLL allows the user to generate high speed system clocks starting from a minimum reference of 4 MHz input clock. Further, the FMPLL supports programmable frequency modulation of the system clock. The PLL multiplication factor and output clock divider ratio are software configurable. The FMPLLs have the following major features:

- Input frequency: 4–40 MHz continuous range (limited by the crystal oscillator)
- Voltage controlled oscillator (VCO) range: 256–512 MHz
- Frequency modulation via software control to reduce and control emission peaks
  - Modulation depth ±2% if centered or 0% to –4% if downshifted via software control register
  - Modulation frequency: triangular modulation with 25 kHz nominal rate
- Option to switch modulation on and off via software interface
- Reduced frequency divider (RFD) for reduced frequency operation without re-lock
- 2 modes of operation
  - Normal PLL mode with crystal reference (default)
  - Normal PLL mode with external reference
- Lock monitor circuitry with lock status
- Loss-of-lock detection for reference and feedback clocks
- Self-clocked mode (SCM) operation
- Auxiliary FMPLL
  - Used for FlexRay due to precise symbol rate requirement by the protocol
  - Used for motor control periphery and connected IP (A/D digital interface CTU) to allow independent frequencies of operation for PWM and timers as well as jitter-free control
  - Option to enable/disable modulation to avoid protocol violation on jitter and/or potential unadjusted error in electric motor control loop
  - Allows running motor control periphery at different (precisely lower, equal, or higher, as required) frequency than the system to ensure higher resolution

Table 3. 257 MAPBGA supply pins (continued)

Ball number	Ball name	Pad type	Ball number	Ball name	Pad type
R9	VDD_HV_ADR_02	VDD_HV_A	M9	VDD_LV_COR	VDD_LV
U9	VDD_HV_ADV	VDD_HV_A	M10	VDD_LV_COR	VDD_LV
F6	VDD_LV_COR	VDD_LV	M11	VDD_LV_COR	VDD_LV
F7	VDD_LV_COR	VDD_LV	M12	VDD_LV_COR	VDD_LV
F8	VDD_LV_COR	VDD_LV	P4	VDD_LV_PLL	VDD_LV
V_{SS}					
A1	VSS_HV_IO	VSS_HV	G7	VSS_LV_COR	VSS_LV
A2	VSS_HV_IO	VSS_HV	G8	VSS_LV_COR	VSS_LV
A16	VSS_HV_IO	VSS_HV	G9	VSS_LV_COR	VSS_LV
A17	VSS_HV_IO	VSS_HV	G10	VSS_LV_COR	VSS_LV
B1	VSS_HV_IO	VSS_HV	G11	VSS_LV_COR	VSS_LV
B2	VSS_HV_IO	VSS_HV	H7	VSS_LV_COR	VSS_LV
B9	VSS_HV_IO	VSS_HV	H8	VSS_LV_COR	VSS_LV
B17	VSS_HV_IO	VSS_HV	H9	VSS_LV_COR	VSS_LV
C3	VSS_HV_IO	VSS_HV	H10	VSS_LV_COR	VSS_LV
D15	VSS_HV_IO	VSS_HV	H11	VSS_LV_COR	VSS_LV
H2	VSS_HV_IO	VSS_HV	J7	VSS_LV_COR	VSS_LV
N2	VSS_HV_IO	VSS_HV	J8	VSS_LV_COR	VSS_LV
P9	VSS_HV_IO	VSS_HV	J9	VSS_LV_COR	VSS_LV
R3	VSS_HV_IO	VSS_HV	J10	VSS_LV_COR	VSS_LV
R15	VSS_HV_IO	VSS_HV	J11	VSS_LV_COR	VSS_LV
T1	VSS_HV_IO	VSS_HV	K7	VSS_LV_COR	VSS_LV
T17	VSS_HV_IO	VSS_HV	K8	VSS_LV_COR	VSS_LV
U1	VSS_HV_IO	VSS_HV	K9	VSS_LV_COR	VSS_LV
U2	VSS_HV_IO	VSS_HV	K10	VSS_LV_COR	VSS_LV
U16	VSS_HV_IO	VSS_HV	K11	VSS_LV_COR	VSS_LV
U17	VSS_HV_IO	VSS_HV	L7	VSS_LV_COR	VSS_LV
D9	VSS_HV_FLA	VSS_HV	L8	VSS_LV_COR	VSS_LV
P1	VSS_HV_OSC	VSS_HV	L9	VSS_LV_COR	VSS_LV
C15	VSS_HV_PDI	VSS_HV	L10	VSS_LV_COR	VSS_LV
J16	VSS_HV_PDI	VSS_HV	L11	VSS_LV_COR	VSS_LV
T9	VSS_HV_ADR_02	VSS_HV_A	N4	VSS_LV_PLL	VSS_LV
T7	VSS_HV_ADR_13	VSS_HV_A	U15	VSS_HV_PMU	VSS_LV
U10	VSS_HV_ADV	VSS_HV_A			

Table 9. 257 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional inputs	Analog inputs	Weak pull during reset	Pad type	Power domain
C7	GPIO	etimer0 ETC[1]	A0: siul_GPIO[1] A1: etimer0_ETC[1] A2: _ A3: _	I: _ I: _ I: siul_EIRQ[1]	—	disabled	GP Slow/ Medium	VDD_HV_IO
C8	GPIO	etimer0 ETC[2]	A0: siul_GPIO[2] A1: etimer0_ETC[2] A2: _ A3: _	I: _ I: _ I: siul_EIRQ[2]	—	disabled	GP Slow/ Medium	VDD_HV_IO
C9	GPIO	etimer0 ETC[3]	A0: siul_GPIO[3] A1: etimer0_ETC[3] A2: _ A3: _	I: _ I: mc_rgm_ABS[2] I: siul_EIRQ[3]	—	pulldown	GP Slow/ Medium	VDD_HV_IO
C11	GPIO	fec CRS	A0: siul_GPIO[208] A1: flexray_DBG1 A2: etimer2_ETC[3] A3: dspi0_CS5	I: fec_CRS I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
C12	GPIO	fec TXD[0]	A0: siul_GPIO[201] A1: fec_TXD[0] A2: etimer2_ETC[1] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
C13	GPIO	fec COL	A0: siul_GPIO[206] A1: fec_COL A2: _ A3: lin1_TXD	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
C14	GPIO	can0 RXD	A0: siul_GPIO[17] A1: _ A2: _ A3: sscm_DEBUG[1]	I: can0_RXD I: can1_RXD I: siul_EIRQ[16]	—	disabled	GP Slow/ Medium	VDD_HV_IO
C16	GPIO	pdi DATA[5]	A0: siul_GPIO[136] A1: flexpwm2_A[0] A2: _ A3: etimer1_ETC[0]	I: pdi_DATA[5] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
C17	GPIO	pdi CLOCK	A0: siul_GPIO[128] A1: flexpwm2_B[1] A2: _ A3: etimer1_ETC[3]	I: pdi_CLOCK I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI

Table 9. 257 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional inputs	Analog inputs	Weak pull during reset	Pad type	Power domain
J17	GPIO	flexpwm0 X[1]	A0: siul_GPIO[195] A1: flexpwm0_X[1] A2: ebi_AD29 A3: _	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_IO
K1	GPIO	nexus MSEO_B[0][1]	A0: siul_GPIO[89] A1: _ A2: npc_wrapper_MSEO_B[0] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
K2	GPIO	nexus MSEO_B[1][1]	A0: siul_GPIO[88] A1: _ A2: npc_wrapper_MSEO_B[1] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
K3	GPIO	nexus RDY_B	A0: siul_GPIO[216] A1: _ A2: nexus_RDY_B A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
K4	GPIO	dspi0 SIN	A0: siul_GPIO[39] A1: _ A2: _ A3: sscm_DEBUG[7]	I: dspi0_SIN I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
K14	GPIO	flexpwm0 X[2]	A0: siul_GPIO[196] A1: flexpwm0_X[2] A2: ebi_AD30 A3: _	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_IO
K15	GPIO	flexpwm0 X[3]	A0: siul_GPIO[197] A1: flexpwm0_X[3] A2: ebi_AD31 A3: _	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_IO
K16	GPIO	flexpwm0 A[1]	A0: siul_GPIO[149] A1: _ A2: ebi_RD_WR A3: flexpwm0_A[1]	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_IO
K17	GPIO	flexpwm0 B[0]	A0: siul_GPIO[148] A1: _ A2: ebi_CLKOUT A3: flexpwm0_B[0]	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_IO

Table 9. 257 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional inputs	Analog inputs	Weak pull during reset	Pad type	Power domain
R4	GPIO	dspi1 CS3	A0: siul_GPIO[55] A1: dspi1_CS3 A2: lin2_TXD A3: dspi0_CS4	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
R5	ANA	adc2 AN[0]	—	siul_GPI[221]	AN: adc2_AN[0]	—	Analog	VDD_HV_ADR02
R6	ANA	adc2 AN[3]	—	siul_GPI[224]	AN: adc2_AN[3]	—	Analog	VDD_HV_ADR02
R8	ANA	adc2_adc3 AN[14]	—	siul_GPI[228]	AN: adc2_adc3_AN[14]	—	Analog Shared	VDD_HV_ADR13
R10	ANA	adc0 AN[2]	—	siul_GPI[33]	AN: adc0_AN[2]	—	Analog	VDD_HV_ADR02
R11	ANA	adc0_adc1 AN[13]	—	siul_GPI[27]	AN: adc0_adc1_AN[13]	—	Analog Shared	VDD_HV_ADR02
R12	ANA	adc1 AN[1]	—	siul_GPI[30] etimer0_ETC[4] siul_EIRQ[19]	AN: adc1_AN[1]	—	Analog	VDD_HV_ADR13
R14	GPIO	lin0 TXD	A0: siul_GPIO[18] A1: lin0_TXD A2: i2c0_clock A3: sscm_DEBUG[2]	I: _ I: _ I: siul_EIRQ[17]	—	disabled	GP Slow/ Medium	VDD_HV_IO
R16	GPIO	flexpwm1 A[2]	A0: siul_GPIO[164] A1: dramc_ADD[6] A2: ebi_ADD14 A3: flexpwm1_A[2]	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_IO
R17	GPIO	flexpwm1 B[2]	A0: siul_GPIO[165] A1: dramc_ADD[7] A2: ebi_ADD15 A3: flexpwm1_B[2]	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_IO

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
B4	GPIO	can1 TXD	A0: siul_GPIO[14] A1: can1_TXD A2: _ A3: _	I: _ I: _ I: siul_EIRQ[13]	—	disabled	GP Slow/ Medium	VDD_HV_IO
B5	GPIO	nexus MDO[14][1]	A0: siul_GPIO[219] A1: _ A2: npc_wrapper_MDO[14] A3: can3_TXD	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
B6	GPIO	dspi2 CS1	A0: siul_GPIO[9] A1: dspi2_CS1 A2: _ A3: _	I: flexpwm0_FAULT[0] I: lin3_RXD I: can2_RXD	—	disabled	GP Slow/ Medium	VDD_HV_IO
B7	GPIO	flexray CB_TR_EN	A0: siul_GPIO[52] A1: flexray_CB_TR_EN A2: _ A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Symmetric	VDD_HV_IO
B8	GPIO	flexray CA_TX	A0: siul_GPIO[48] A1: flexray_CA_TX A2: _ A3: _	I: ctu1_EXT_IN I: _ I: _	—	disabled	GP Slow/ Symmetric	VDD_HV_IO
B9	GPIO	fec RXD[3]	A0: siul_GPIO[214] A1: i2c1_data A2: _ A3: _	I: fec_RXD[3] I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
B10	GPIO	fec RX_ER	A0: siul_GPIO[215] A1: _ A2: _ A3: dspi0_CS1	I: fec_RX_ER I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
B11	GPIO	fec TXD[0]	A0: siul_GPIO[201] A1: fec_TXD[0] A2: etimer2_ETC[1] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
B12	GPIO	fec RXD[0]	A0: siul_GPIO[211] A1: i2c1_clock A2: _ A3: _	I: fec_RXD[0] I: _ I: siul_EIRQ[27]	—	disabled	GP Slow/ Medium	VDD_HV_IO

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
U20	GPIO	dramc ADD[6]	A0: siul_GPIO[164] A1: dramc_ADD[6] A2: ebi_ADD14 A3: flexpwm1_A[2]	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
U21	GPIO	dramc ADD[12]	A0: siul_GPIO[170] A1: dramc_ADD[12] A2: ebi_AD4 A3: ebi_ADD20	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
U23	GPIO	dramc ADD[0]	A0: siul_GPIO[158] A1: dramc_ADD[0] A2: ebi_ADD8 A3: ebi_CS2	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
V3	GPIO	flexpwm1 B[2]	A0: siul_GPIO[124] A1: flexpwm1_B[2] A2: _ A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
V4	GPIO	dspi1 CS2	A0: siul_GPIO[56] A1: dspi1_CS2 A2: _ A3: dspi0_CS5	I: flexpwm0_FAULT[3] I: lin2_RXD I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
V20	GPIO	lin0 TXD	A0: siul_GPIO[18] A1: lin0_TXD A2: i2c0_clock A3: sscm_DEBUG[2]	I: _ I: _ I: siul_EIRQ[17]	—	disabled	GP Slow/ Medium	VDD_HV_IO
V21	GPIO	dramc ADD[13]	A0: siul_GPIO[171] A1: dramc_ADD[13] A2: ebi_AD5 A3: ebi_ADD21	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
V23	GPIO	dramc ADD[2]	A0: siul_GPIO[160] A1: dramc_ADD[2] A2: ebi_ADD10 A3: ebi_TA	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
W3	GPIO	dspi0 CS3	A0: siul_GPIO[53] A1: dspi0_CS3 A2: i2c2_clock A3: _	I: flexpwm0_FAULT[2] I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
AA14	ANA	adc0_adc1 AN[12]	—	siul_GPI[26]	AN: adc0_adc1_AN[12]	—	Analog Shared	VDD_HV_ADR0
AA15	ANA	adc1 AN[0]	—	siul_GPI[29] lin1_RXD	AN: adc1_AN[0]	—	Analog	VDD_HV_ADR1
AA16	ANA	adc1 AN[2]	—	siul_GPI[31] siul_EIRQ[20]	AN: adc1_AN[2]	—	Analog	VDD_HV_ADR1
AA17	ANA	adc1 AN[5]	—	siul_GPI[64]	AN: adc1_AN[5]	—	Analog	VDD_HV_ADR1
AA18	ANA	adc1 AN[7]	—	siul_GPI[73]	AN: adc1_AN[7]	—	Analog	VDD_HV_ADR1
AA19	GPIO	TDI	A0: siul_GPIO[21] A1: _ A2: _ A3: _	I: jtagc_TDI I: _ I: _	—	pullup	GP Slow/ Medium	VDD_HV_IO
AA20	GPIO	etimer1 ETC[0]	A0: siul_GPIO[4] A1: etimer1_ETC[0] A2: _ A3: _	I: _ I: _ I: siul_EIRQ[4]	—	disabled	GP Slow/ Medium	VDD_HV_IO
AA22	GPIO	lin1 TXD	A0: siul_GPIO[94] A1: lin1_TXD A2: i2c1_clock A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
AA23	GPIO	dramc ADD[10]	A0: siul_GPIO[168] A1: dramc_ADD[10] A2: ebi_AD2 A3: ebi_ADD18	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
AB3	GPIO	dspi2 SOUT	A0: siul_GPIO[12] A1: dspi2_SOUT A2: _ A3: _	I: _ I: _ I: siul_EIRQ[11]	—	disabled	GP Slow/ Medium	VDD_HV_IO

3 Electrical characteristics

3.1 Introduction

This section contains detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications for this device.

The “Symbol” column of the electrical parameter and timings tables may contain an additional column containing “SR”, “CC”, “P”, “C”, “T”, or “D”.

- “SR” identifies system requirements—conditions that must be provided to ensure normal device operation. An example is the *input* voltage of a voltage regulator.
- “CC” identifies specifications that define normal device operation. Where available, the letters “P”, “C”, “T”, or “D” replace the letter “CC” and apply to these controller characteristics. They specify how each characteristic is guaranteed.
  - P: parameter is guaranteed by production testing of each individual device.
  - C: parameter is guaranteed by design characterization. Measurements are taken from a statistically relevant sample size across process variations.
  - T: parameter is guaranteed by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values are shown in the typical (“typ”) column are within this category.
  - D: parameters are derived mainly from simulations.

3.2 Absolute maximum ratings

Table 11. Absolute maximum ratings[1]

No.	Symbol		Parameter	Conditions	Min	Max	Unit
1	$V_{DD\_HV\_PMU}$	SR	Voltage regulator supply voltage	—	–0.3	5.5[2]	V
2	$V_{SS\_HV\_PMU}$	SR	Voltage regulator supply ground	—	–0.1	0.1	V
3	$V_{DD\_HV\_IO}$	SR	Input/output supply voltage	—	–0.3	3.6[3,4]	V
4	$V_{SS\_HV\_IO}$	SR	Input/output supply ground	—	–0.1	0.1	V
5	$V_{DD\_HV\_FLA}$	SR	Flash supply voltage	—	–0.3	3.6[3,4]	V
6	$V_{SS\_HV\_FLA}$	SR	Flash supply ground	—	–0.1	0.1	V
7	$V_{DD\_HV\_OSC}$	SR	Crystal oscillator amplifier supply voltage	—	–0.3	3.6[3,4]	V
8	$V_{SS\_HV\_OSC}$	SR	Crystal oscillator amplifier supply ground	—	–0.1	0.1	V
9	$V_{DD\_HV\_PDI}$	SR	PDI interface supply voltage	—	–0.3	3.6[3,4]	V
10	$V_{SS\_HV\_PDI}$	SR	PDI interface supply ground	—	–0.1	0.1	V
11	$V_{DD\_HV\_DRAM}$[5]	SR	DRAM interface supply voltage	—	–0.3	3.6[3,4]	V
12	$V_{SS\_HV\_DRAM}$	SR	DRAM interface supply ground	—	–0.1	0.1	V
13	$V_{DD\_HV\_ADRx}$[6]	SR	ADC*x* high reference voltage	—	–0.3	6.0	V
14	$V_{SS\_HV\_ADRx}$	SR	ADC*x* low reference voltage	—	–0.1	0.1	V
15	$V_{DD\_HV\_ADV}$	SR	ADC supply voltage	—	–0.3	3.6[3,4]	V
16	$V_{SS\_HV\_ADV}$	SR	ADC supply ground	—	–0.1	0.1	V
17	$V_{DD\_LV\_COR}$	SR	Core supply voltage digital logic	—	–0.3	1.32[7]	V

3 "Loss of Reference Frequency" window is the reference frequency range outside of which the FMPLL is in self clocked mode.

4 Self clocked mode frequency is the frequency that the FMPLL operates at when the reference frequency falls outside the f_{LOR} window.

5 f_{VCO} is the frequency at the output of the VCO; its range is 256–512 MHz.
f_{SCM} is the self-clocked mode frequency (free running frequency); its range is 20–150 MHz.
$f_{sys} = f_{VCO} \div ODF$

6 This value is determined by the crystal manufacturer and board design. For 4 MHz to 20 MHz crystals specified for this FMPLL, load capacitors should not exceed these limits.

7 This specification applies to the period required for the FMPLL to relock after changing the MFD frequency control bits in the synthesizer control register (SYNCR).

8 This value is determined by the crystal manufacturer and board design.

9 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum $f_{FMPLLOUT}$. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FMPLL circuitry via V_{DDPLL} and V_{SSPLL} and variation in crystal oscillator frequency increase the C_{JITTER} percentage for a given interval.

10 Proper PC board layout procedures must be followed to achieve specifications.

11 Values are with frequency modulation disabled. If frequency modulation is enabled, jitter is the sum of C_{JITTER} and either f_{CS} or f_{DS} (depending on whether center spread or down spread modulation is enabled).

12 Core operating at 180 MHz.

13 Modulation depth is attenuated from depth setting when operating at modulation frequencies above 50 kHz.

14 PLL Loop Division Factor (LDF).

3.13 16 MHz RC oscillator electrical characteristics

Table 23. RC oscillator electrical characteristics

No.	Symbol		Parameter	Conditions	Min	Typ	Max	Unit
1	f_{RC}	CC	RC oscillator frequency	25 °C, 1.2 V trimmed	—	16	—	MHz
2	Δ_{RCMVAR}	CC	Frequency spread: The variation in output frequency from PTF[1] across temperature and supply voltage range	—	—	—	±5	%
3	$\Delta_{IRCTRIM}$	CC	Internal RC oscillator trimming step	T_A = 25 °C	—	1.6	—	%

1 PTF = Post Trimming Frequency: The frequency of the output clock after trimming at typical supply voltage and temperature.

3.14 ADC electrical characteristics

The MPC5675K provides a 12-bit Successive Approximation Register (SAR) Analog-to-Digital Converter.

2 Initial Max program and erase times provide guidance for time-out limits used in the factory and apply for < 100 program/erase cycles, nominal supply values and operation at T_J = 25 °C. These values are verified at production test.

3 Lifetime Max program and erase times apply across the voltage, temperature, and cycling range of product life. These values are characterized, but not tested.

4 Actual hardware programming times. This does not include software overhead.

Table 26 shows the data flash memory program and erase characteristics.

Table 26. Data flash memory program and erase electrical specifications

No.	Symbol		Parameter	Min	Typ[1]	Initial max[2]	Lifetime max[3]	Unit
1	$T_{DWPROGRAM}$	CC	Doubleword (64 bits) program time[4]	—	30	70	300	µs
2	$T_{16KPPERASE}$	CC	16 KB block pre-program and erase time	—	700	800	1500	ms

1 Typical program and erase times assume nominal supply values and operation at 25 °C. All times are subject to change pending device characterization.

2 Initial Max program and erase times provide guidance for time-out limits used in the factory and apply for < 100 program/erase cycles, nominal supply values and operation at T_J = 25 °C. These values are verified at production test.

3 Lifetime Max program and erase times apply across the voltage, temperature, and cycling range of product life. These values are characterized, but not tested.

4 Actual hardware programming times. This does not include software overhead.

Table 27. Flash memory module life

No.	Symbol		Parameter	Condition	Value			Unit
					Min	Typ[1]	Max	
1a	P/E	CC	Number of program/erase cycles per block for over the operating temperature range (T_J)	16 KB blocks	100,000	—	—	cycles
1b				32 KB and 64 KB blocks	10,000	100,000	—	cycles
1c				128 KB blocks	1,000	100,000	—	cycles
2	Retention	CC	Minimum data retention at 85 °C average ambient temperature[2]	Blocks with 0–1,000 P/E cycles	20	—	—	years
				Blocks with 1,001–10,000 P/E cycles	10	—	—	years
				Blocks with 10,001–100,000 P/E cycles	5	—	—	years

1 Typical endurance is evaluated at 25 °C. Product qualification is performed to the minimum specification. For additional information on the Freescale definition of Typical Endurance, please refer to Engineering Bulletin EB619, *Typical Endurance for Nonvolatile Memory*.

2 Ambient temperature averaged over duration of application, not to exceed product operating temperature range.

3.17.2 GP pads AC specifications

Table 34. GP pads AC electrical characteristics[1]

No.	Pad	Tswitchon[1] (ns)			Rise/Fall[2] (ns)			Frequency (MHz)			Current slew[3] (mA/ns)			Load drive (pF)
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
1	Slow	3	—	40	4	—	40	—	—	4	0.01	—	2	25
		3	—	40	6	—	50	—	—	2	0.01	—	2	50
		3	—	40	10	—	75	—	—	2	0.01	—	2	100
		3	—	40	14	—	100	—	—	2	0.01	—	2	200
2	Medium	1	—	15	2	—	12	—	—	40	2.5	—	7	25
		1	—	15	4	—	25	—	—	20	2.5	—	7	50
		1	—	15	8	—	40	—	—	13	2.5	—	7	100
		1	—	15	14	—	70	—	—	7	2.5	—	7	200
3	Fast	1	—	6	1	—	4	—	—	72	3	—	40	25
		1	—	6	1.5	—	7	—	—	55	7	—	40	50
		1	—	6	3	—	12	—	—	40	7	—	40	100
		1	—	6	5	—	18	—	—	25	7	—	40	200
4	Symmetric	1	—	8	1	—	5	—	—	50	3	—	25	25
5	Pullup/down (3.6 V max)	—	—	—	—	—	7500	—	—	—	—	—	—	50

1 The values provided in this table are not applicable for PDI and EBI/DRAM interface.

2 Slope at rising/falling edge.

3 Data based on characterization results, not tested in production.

3.18 PDI pads specifications

This section specifies the electrical characteristics of the PDI pads. Please refer to the tables in Section 2.2, Pin descriptions, for a cross reference between package pins and pad types.

PDI pads feature list:

- Direction
  - Input
  - Output
  - Bidirectional
- Driver
  - Push/Pull/Open Drain
  - Configurable Four Drive Strengths on Fast driver pads
  - Configurable No Slew-Rate, Slow Slew-Rate, and Fast Slew-Rate on Slow, Medium, and SLR driver pads
  - VDD_HV_PDI NOTE: All pads are NOT 5 V TOLERANT. Pads are not capable of driving to or from voltages above their respective VDD_HV_PDI. In other words, you cannot connect a 3.3V external device to a pad

supplied with 2.5 V. If a pad must be connected to a 3.3V device, its local VDD_HV_PDI must be 3.3 V. Injection current is then handled by the intrinsic diodes from the pad transistors and by the ESD diodes.

  - VDD_HV_PDI range 1.8 V to 3.3 V, as specified in the following tables
- Receiver
  - Selectable hysteresis input buffer
  - CMOS Input Buffer

The electrical data provided in this section applies:

- To the pads listed in Table 35
- Over the voltage range 1.62–3.6 V

Table 35. PDI I/O pads

No.	Name	Voltage	Used for	Notes
1	PDI Fast	1.62–3.6 V	I/O	Enhanced operating voltage range fast slew-rate output with four selectable slew-rates. Contains an input buffer and weak pullup/pulldown.
2	PDI Medium			Enhanced operating voltage range medium slew-rate output with four selectable slew-rates. Contains an input buffer and weak pullup/pulldown.

Table 36. PDI pads DC electrical characteristics[1]

No.	Symbol		Parameter	Min	Max	Unit
1	$V_{DD\_HV\_PDI}$	SR	I/O supply voltage	1.62	3.6	V
2	V_{IH_C}	CC	CMOS input buffer high voltage (hysteresis enabled)	$0.65 \times V_{DD\_HV\_PDI}$	$V_{DD\_HV\_PDI} + 0.3$	V
3	V_{IH_C}	CC	CMOS input buffer high voltage (hysteresis disabled)	$0.58 \times V_{DD\_HV\_PDI}$	$V_{DD\_HV\_PDI} + 0.3$	V
4	V_{IL_C}	CC	CMOS input buffer low voltage (hysteresis enabled)	$V_{SS} - 0.3$	$0.35 \times V_{DD\_HV\_PDI}$	V
5	V_{IL_C}	CC	CMOS input buffer low voltage (hysteresis disabled)	$V_{SS} - 0.3$	$0.42 \times V_{DD\_HV\_PDI}$	V
6	V_{HYS_C}	CC	CMOS input buffer hysteresis	$0.1 \times V_{DD\_HV\_PDI}$	—	V
7	I_{ACT_S}	CC	Selectable weak pullup/pulldown current	25	150	µA
8	V_{OH}	CC	Output high voltage	$0.8 \times V_{DD\_HV\_PDI}$	—	V
9	V_{OL}	CC	Output low voltage	—	$0.2 \times V_{DD\_HV\_PDI}$	V

1 Over- and undershoots occurring due to impedance mismatch of the external driver and the transmission line at PDI pads in input mode can be allowed up to 0.7 V repeatedly throughout the product expected lifetime and will not cause any long term reliability issue.

Table 37. Drive current

Pad	Drive Mode	Minimum I_{OH} (mA)[1]	Minimum I_{OL} (mA)[2]
PDI Fast	All	26.2	84.8
PDI Medium	All	19.2	52.1

1 I_{OH} is defined as the current sourced by the pad to drive the output to V_{OH}.

2 I_{OL} is defined as the current sunk by the pad to drive the output to V_{OL}.

3.21.4.3 External reset via $\overline{\text{RESET}}$

Figure 20 shows the voltage thresholds that determine the start of the reset sequences initiated by the assertion of $\overline{\text{RESET}}$ as specified in Table 53.

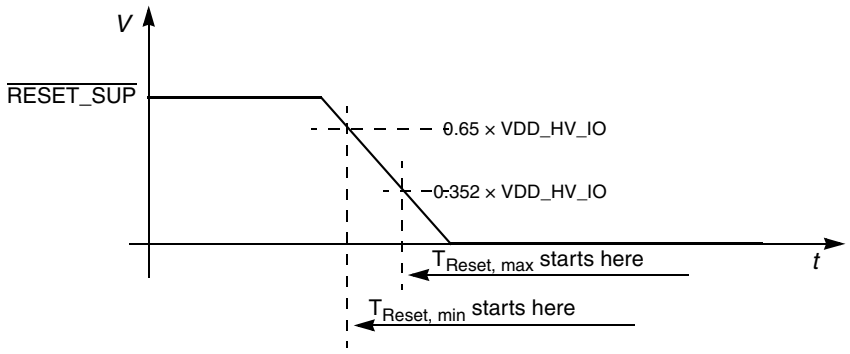

Figure 20. Reset sequence start via $\overline{\text{RESET}}$ assertion

3.21.5 External watchdog window

If the application design requires the use of an external watchdog the data provided in Section 3.21, Reset sequence can be used to determine the correct positioning of the trigger window for the external watchdog. Figure 21 shows the relationships between the minimum and the maximum duration of a given reset sequence and the position of an external watchdog trigger window.

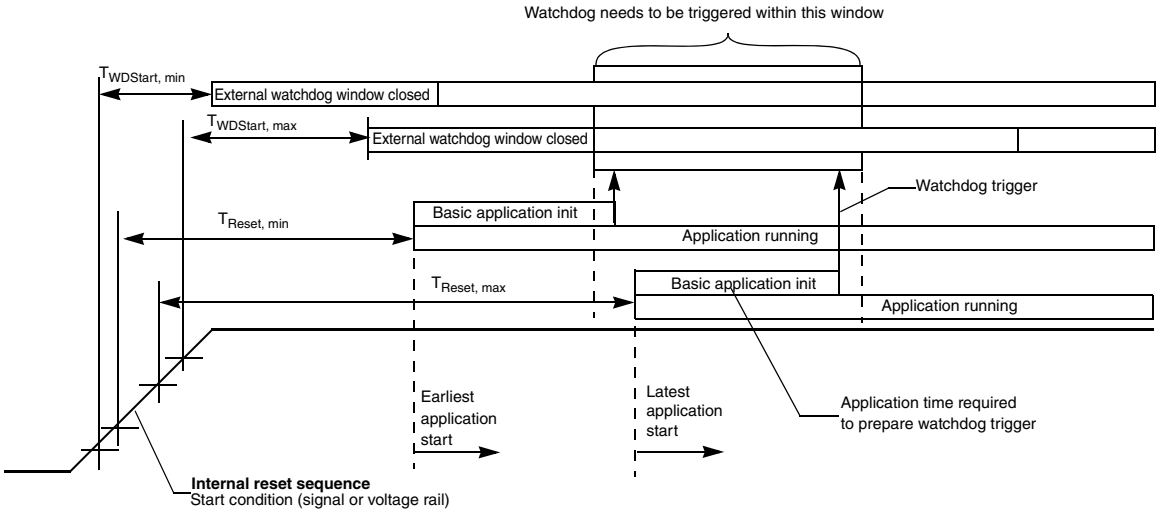

Figure 21. Reset sequence—external watchdog trigger window position

3.22 Peripheral timing characteristics

3.22.1 SDRAM (DDR)

The MPC5675K memory controller supports three types of DDR devices:

- DDR-1 (SSTL_2 class II interface)
- DDR-2 (SSTL_18 interface)
- LPDDR/Mobile-DDR (1.8V I/O supply voltage)

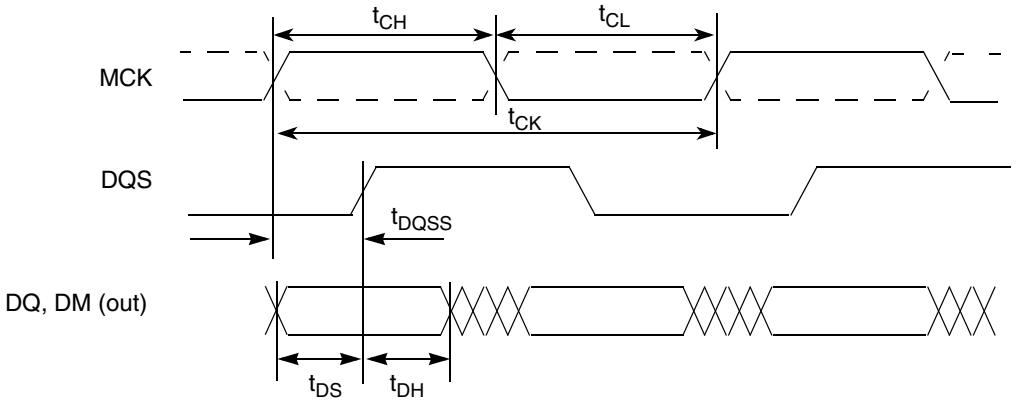

Figure 22. DDR write timing

Figure 23 and Figure 24 show the DDR SDRAM read timing.

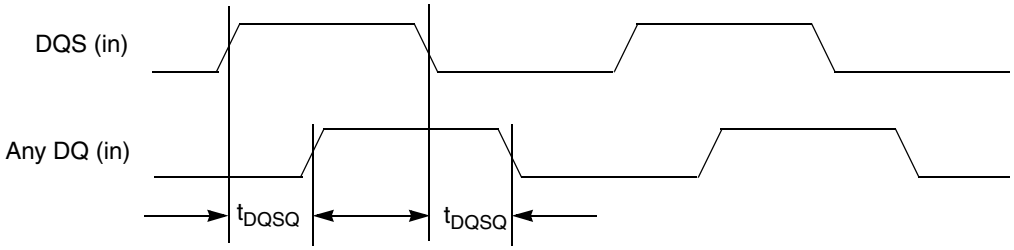

Figure 23. DDR read timing, DQ vs. DQS

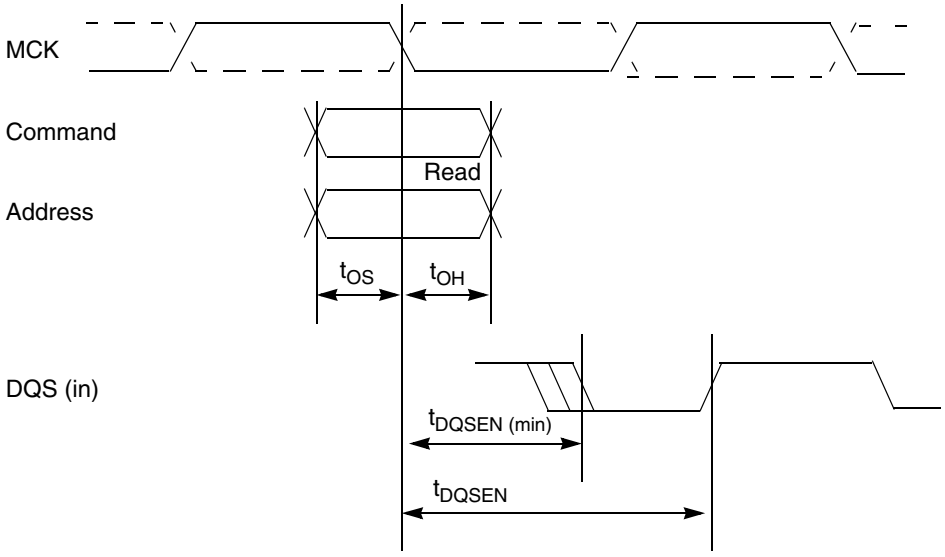

Figure 24. DDR read timing, DQSEN

Figure 25 provides the AC test load for the DDR bus.

[1] $f_{TCK} = 1/t_{TCK}$. f_{TCK} needs to be smaller than the system clock (SYS_CLK). This frequency is valid only in special modes where TDO is sampled at the next falling edge for Core0/1 Nexus TAPs and hence full cycle is given to TDO for settling before it is sampled.

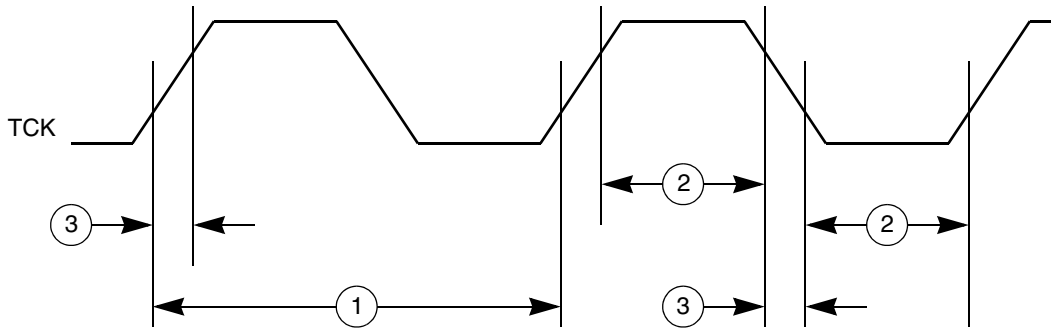

Figure 26. JTAG test clock input timing

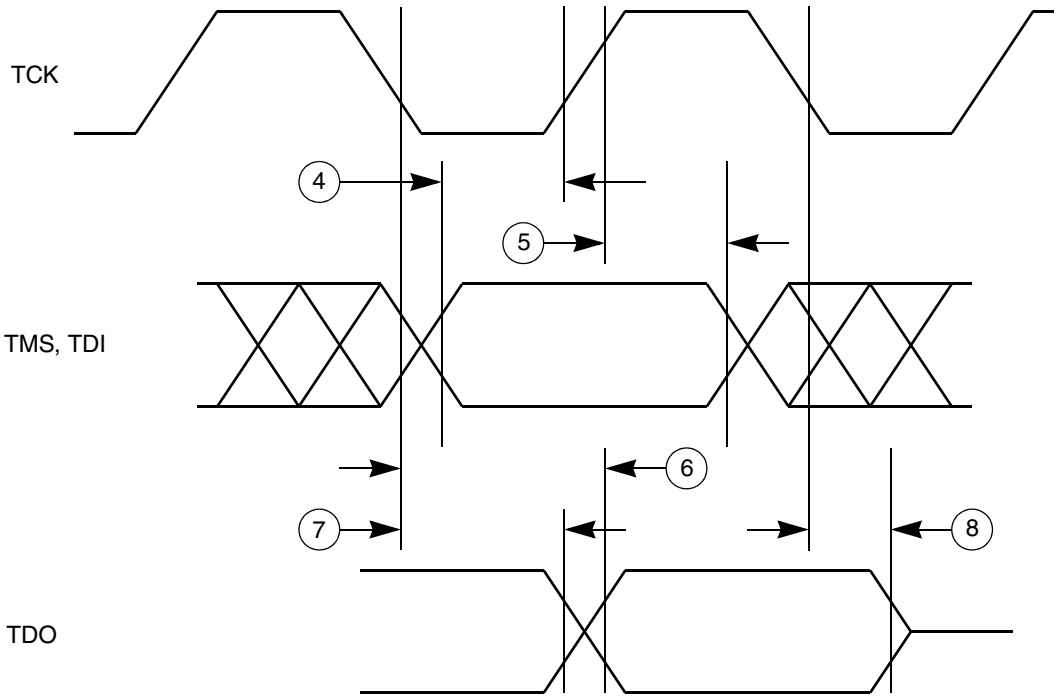

Figure 27. JTAG test access port timing

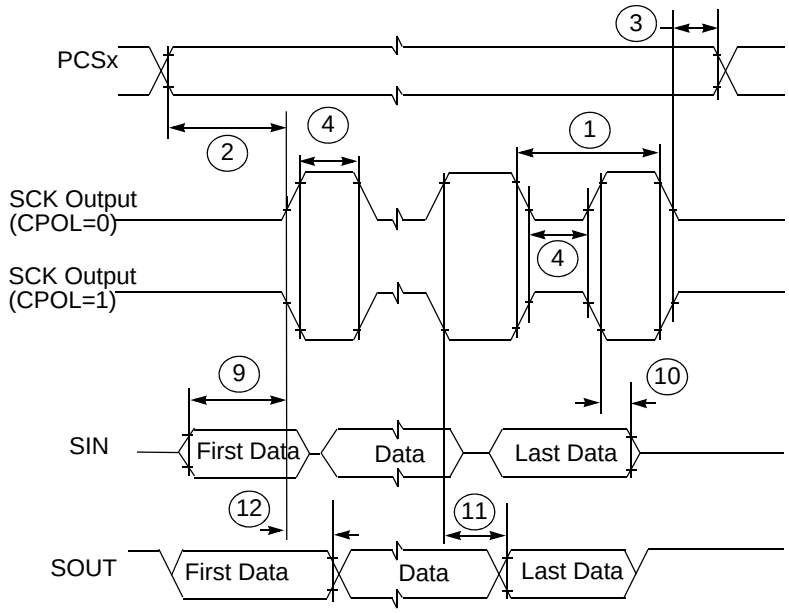

Figure 37. DSPI modified transfer format timing—master, CPHA = 0

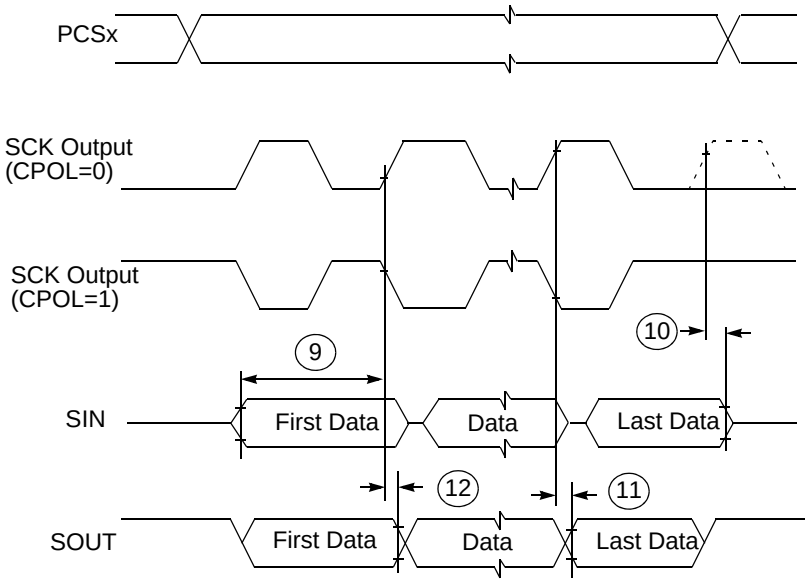

Figure 38. DSPI modified transfer format timing—master, CPHA = 1

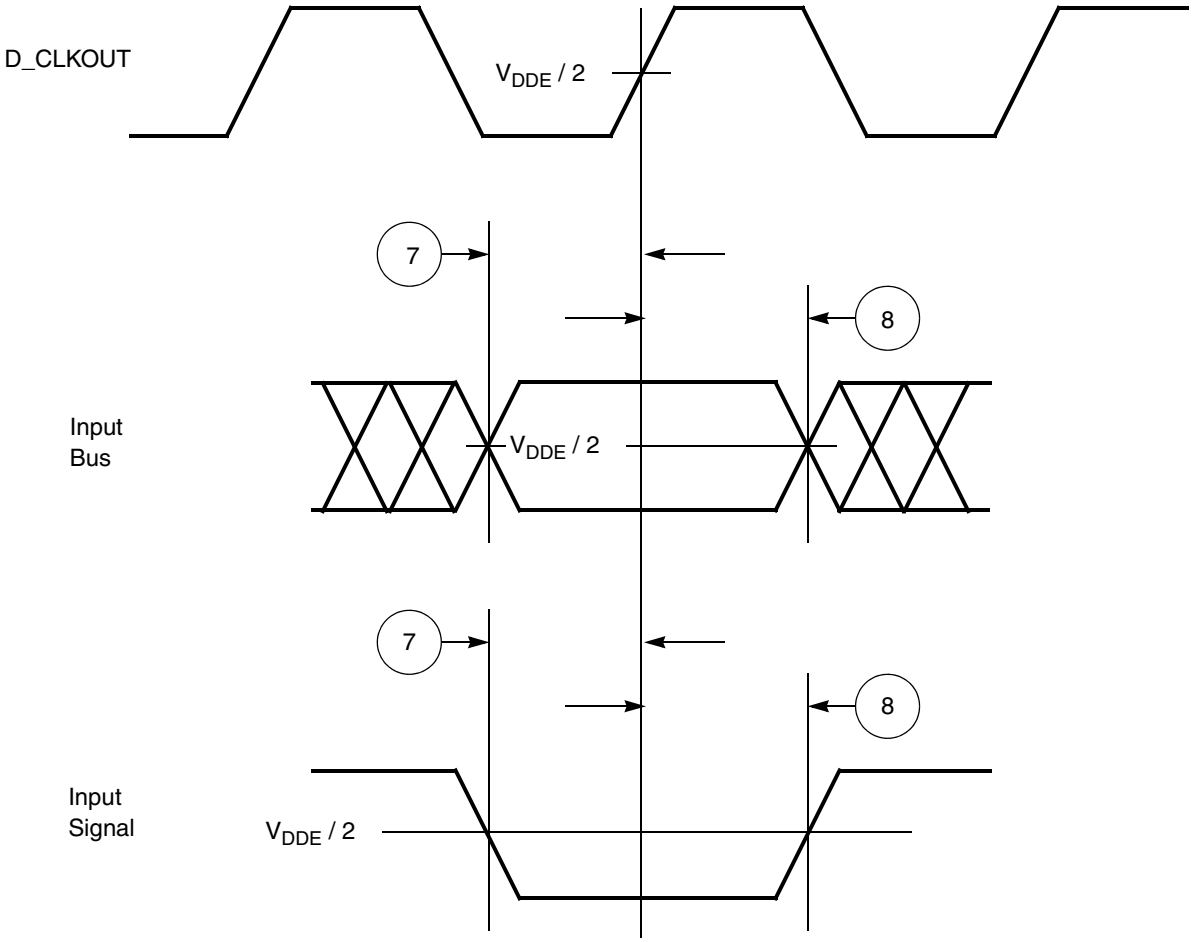

Figure 51. Synchronous input timing

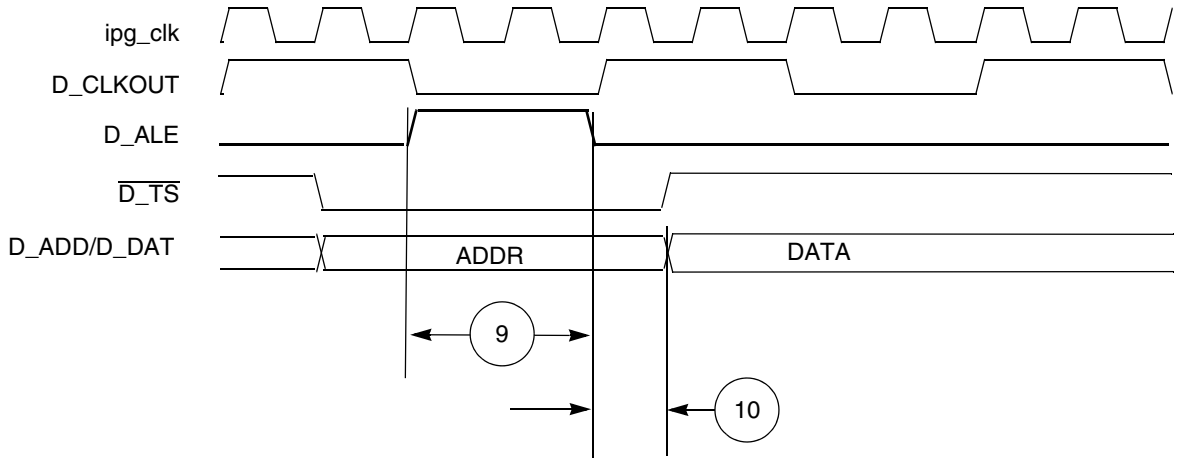

Figure 52. ALE signal timing

REVISION HISTORY

DOCUMENT NO: 98ASA00096D
PAGE: 2089
REV: O

LTR	ORIGINATOR	REVISIONS	DRAFTER	DATE
O	D. VO	RELEASED FOR PRODUCTION	DSS	08 JUN 2009

TITLE:	CASE NUMBER: 2089–01	
473 I/O, FINE PITCH, PBGA, 19 X 19 PKG, 0.8MM PITCH (MAP)	STANDARD: NON–JEDEC	
	PACKAGE CODE:IN AGILE	SHEET: 3

Figure 58. 473 MAPBGA package mechanical data (3 of 3)